

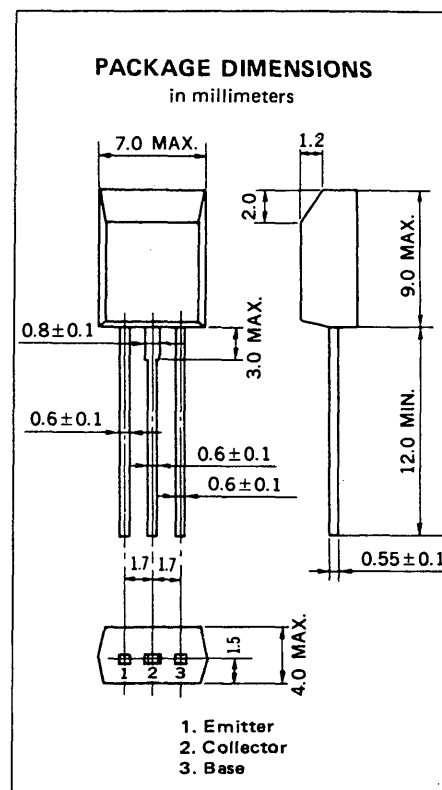
NPN SILICON TRANSISTOR 2SC4000

DESCRIPTION The 2SC4000 is designed for uses of high-resolution monitor TV applications. This makes it possible to raise the video band of high-resolution monitor TVs to 50 MHz.

- FEATURES**
- High f_T : $f_T = 300$ MHz TYP. (@ $V_{CE} = 30$ V, $I_E = -30$ mA)
 - Low C_{ob} : $C_{ob} = 2.8$ pF (@ $V_{CB} = 30$ V)
 - High Voltage: $V_{CBO} = 300$ V, $V_{CEO} = 250$ V
 - High Total Power Dissipation: $P_T = 1.0$ W
 - Complementary to 2SA1545

ABSOLUTE MAXIMUM RATINGS

Maximum Temperatures			
Storage Temperature		-55 to +150 °C	
Junction Temperature		150 °C Maximum	
Maximum Power Dissipation ($T_a = 25$ °C)			
Total Power Dissipation		1.0 W	
Maximum Voltages and Current ($T_a = 25$ °C)			
V_{CBO}	Collector to Base Voltage	300	V
V_{CEO}	Collector to Emitter Voltage	250	V
V_{EBO}	Emitter to Base Voltage	5.0	V
I_C	Collector Current	100	mA



ELECTRICAL CHARACTERISTICS ($T_a = 25$ °C)

SYMBOL	CHARACTERISTIC	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
h_{FE}	DC Current Gain	60	200	320	—	$V_{CE} = 10$ V, $I_C = 10$ mA*
f_T	Gain Bandwidth Product	200	300		MHz	$V_{CE} = 30$ V, $I_E = -30$ mA
C_{ob}	Output Capacitance		2.8	3.5	pF	$V_{CB} = 30$ V, $I_E = 0$, $f = 1$ MHz
I_{CBO}	Collector Cutoff Current			100	nA	$V_{CB} = 200$ V, $I_E = 0$
I_{EBO}	Emitter Cutoff Current			100	nA	$V_{EB} = 3.0$ V, $I_C = 0$
$V_{CE(sat)}$	Collector Saturation Voltage		0.08	0.3	V	$I_C = 10$ mA, $I_B = 1.0$ mA*
$V_{BE(sat)}$	Base Saturation Voltage		0.72	1.2	V	$I_C = 10$ mA, $I_B = 1.0$ mA*
V_{ESDR}	Electrostatic Discharge-Resistant		1 000		V	$C = 1 000$ pF, E-B Reverse Bias

* Pulsed PW < 350 μ s, Duty Cycle < 2 %

Classification of h_{FE}

Rank	M	L	K
Range	60 to 120	100 to 200	160 to 320

Test Conditions: $V_{CE} = 10$ V, $I_C = 10$ mA

TYPICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

